

August 2014

FDPF33N25T

N-Channel UniFETTM MOSFET 250 V, 33 A, 94 m Ω

Features

- $R_{DS(on)}$ = 94 m Ω (Max.) @ V_{GS} = 10 V, I_D = 16.5 A
- Low Gate Charge (Typ. 36.8 nC)
- Low C_{rss} (Typ. 39 pF)
- 100% Avalanche Tested

Applications

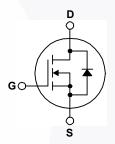
- PDP TV
- · Lighting
- · Uninterruptible Power Supply
- · AC-DC Power Supply

Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.







Absolute Maximum Ratings $T_C = 25$ °C unless otherwise noted.

Symbol		Parameter	FDPF33N25T FDPF33N25TRDTU	Unit
V_{DSS}	Drain-Source Voltage	250	V	
I _D	Drain Current	- Continuous (T _C = 25°C) - Continuous (T _C = 100°C)	33* 20.4*	A A
I _{DM}	Drain Current	- Pulsed (Note 1)	132*	Α
V_{GSS}	Gate-Source voltage	± 30	V	
E _{AS}	Single Pulsed Avalanche	e Energy (Note 2)	918	mJ
I _{AR}	Avalanche Current	33	Α	
E _{AR}	Repetitive Avalanche En	23.5	mJ	
dv/dt	Peak Diode Recovery dv	4.5	V/ns	
P _D	Power Dissipation (T _C = 25°C) - Derate Above 25°C		37 0.29	W/°C
T _J , T _{STG}	Operating and Storage	-55 to +150	°C	
T _L	Maximum Lead Tempera	ature for Soldering, 1/8" from Case for 5 Seconds	300	°C

^{*}Drain current limited by maximum junction temperature.

Thermal Characteristics

Symbol	Parameter	FDPF33N25T FDPF33N25TRDTU	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case, Max.	3.4	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	62.5	°C/W

Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FDPF33N25T	FDPF33N25T	TO-220F	Tube	N/A	N/A	50 units
FDPF33N25TRDTU	FDPF33N25T	TO-220F (LG-formed)	Tube	N/A	N/A	50 units

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	I Parameter Conditions		Min.	Тур.	Max.	Unit
Off Charac	cteristics			•		
BV _{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0 V, I_{D} = 250 μ A, T_{J} = 25°C	250			V
ΔBV _{DSS} / ΔT _J	Breakdown Voltage Temperature Coefficient	I _D = 250 μA, Referenced to 25°C		0.25		V/°C
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 250 V, V _{GS} = 0 V V _{DS} = 200 V, T _C = 125°C			1 10	μA μA
I _{GSSF}	Gate-Body Leakage Current, Forward	V _{GS} = 30 V, V _{DS} = 0 V			100	nA
I _{GSSR}	Gate-Body Leakage Current, Reverse	V _{GS} = -30 V, V _{DS} = 0 V			-100	nA
On Charac	teristics					
V _{GS(th)}	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R _{DS(on)}	Static Drain-Source On-Resistance	V _{GS} = 10 V, I _D = 16.5 A		0.077	0.094	Ω
9 _{FS}	Forward Transconductance	V _{DS} = 40 V, I _D = 16.5 A		26.6		S
Dynamic C	Characteristics					
C _{iss}	Input Capacitance	V _{DS} = 25 V, V _{GS} = 0 V,		1640	2135	pF
C _{oss}	Output Capacitance	f = 1.0 MHz		330	430	pF
C _{rss}	Reverse Transfer Capacitance			39	59	pF
Switching	Characteristics					
t _{d(on)}	Turn-On Delay Time	V _{DD} = 125 V, I _D = 33 A,		35	80	ns
t _r	Turn-On Rise Time	V_{GS} = 10 V, R_G = 25 Ω		230	470	ns
t _{d(off)}	Turn-Off Delay Time			75	160	ns
t _f	Turn-Off Fall Time	(Note 4)		120	250	ns
Qg	Total Gate Charge	$V_{DS} = 200 \text{ V}, I_{D} = 33 \text{ A},$		36.8	48	nC
Q_{gs}	Gate-Source Charge	V _{GS} = 10 V		10		nC
Q_{gd}	Gate-Drain Charge	(Note 4)		17		nC
Drain-Sou	rce Diode Characteristics and Maximun	n Ratings				
I _S	Maximum Continuous Drain-Source Diode Forward Current				33	Α
I _{SM}	Maximum Pulsed Drain-Source Diode F	Diode Forward Current			132	Α
V_{SD}	Drain-Source Diode Forward Voltage	V _{GS} = 0 V, I _S = 33 A			1.4	٧
t _{rr}	Reverse Recovery Time	V _{GS} = 0 V, I _S = 33 A,		220		ns
Q _{rr}	Reverse Recovery Charge	dl _F /dt =100 A/μs		1.71		μС

Notes

^{1.} Repetitive rating: pulse-width limited by maximum junction temperature.

^{2.} L = 1.35 mH, I_{AS} = 33 A, V_{DD} = 50 V, R_{G} = 25 Ω , starting T_{J} = 25°C.

^{3.} I $_{SD} \leq$ 33 A, di/dt \leq 200 A/µs, V $_{DD} \leq$ BV $_{DSS}$, starting T $_{J}$ = 25°C.

^{4.} Essentially independent of operating temperature typical characteristics.

Typical Performance Characteristics

Figure 1. On-Region Characteristics

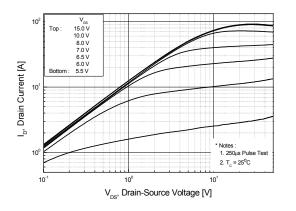
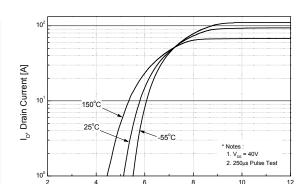


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage



 $V_{\rm GS}$, Gate-Source Voltage [V]

Figure 2. Transfer Characteristics

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

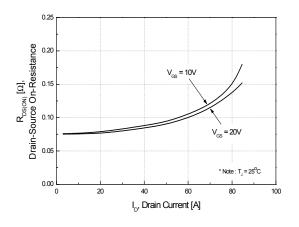
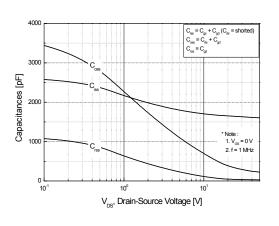


Figure 5. Capacitance Characteristics



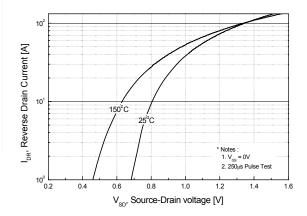
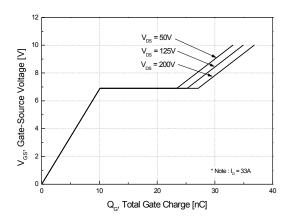


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

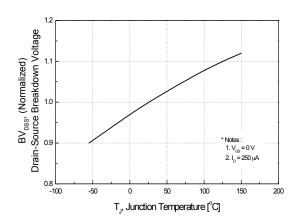


Figure 9. Maximum Safe Operating Area

Figure 8. On-Resistance Variation vs. Temperature

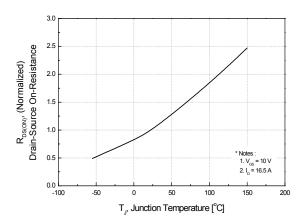
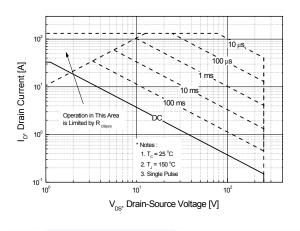


Figure 10. Maximum Drain Current vs. Case Temperature



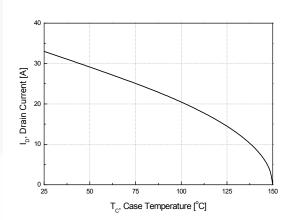
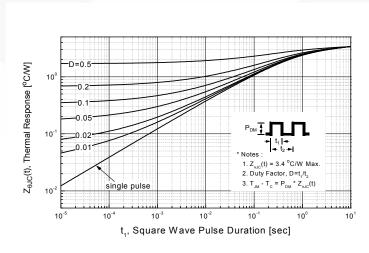


Figure 11. Transient Thermal Response Curve



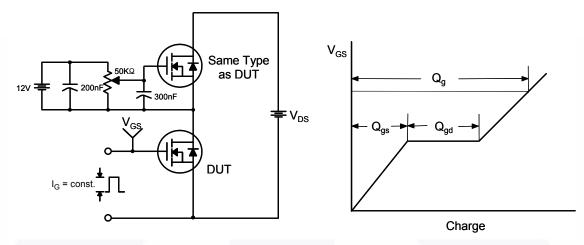


Figure 12. Gate Charge Test Circuit & Waveform

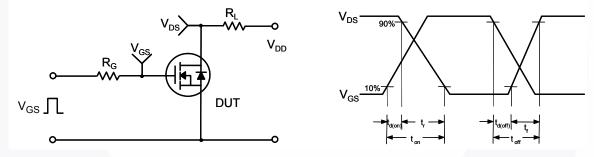


Figure 13. Resistive Switching Test Circuit & Waveforms

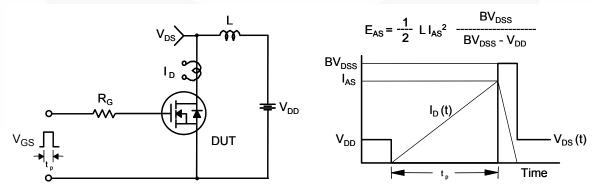


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms

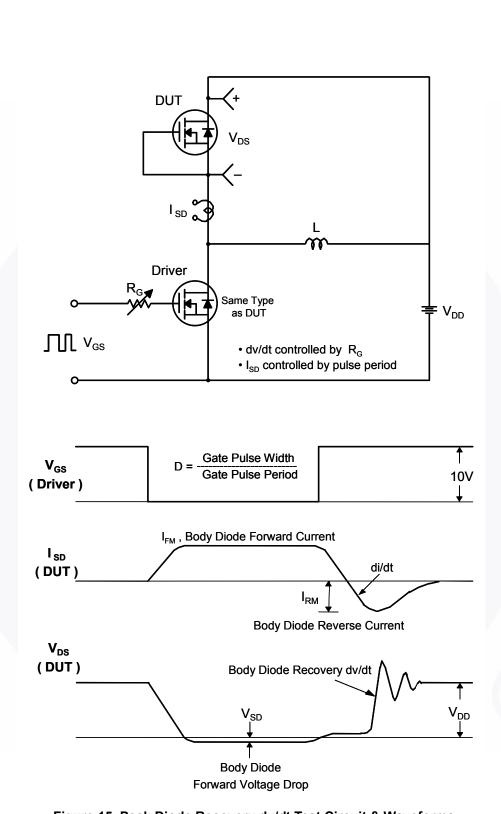
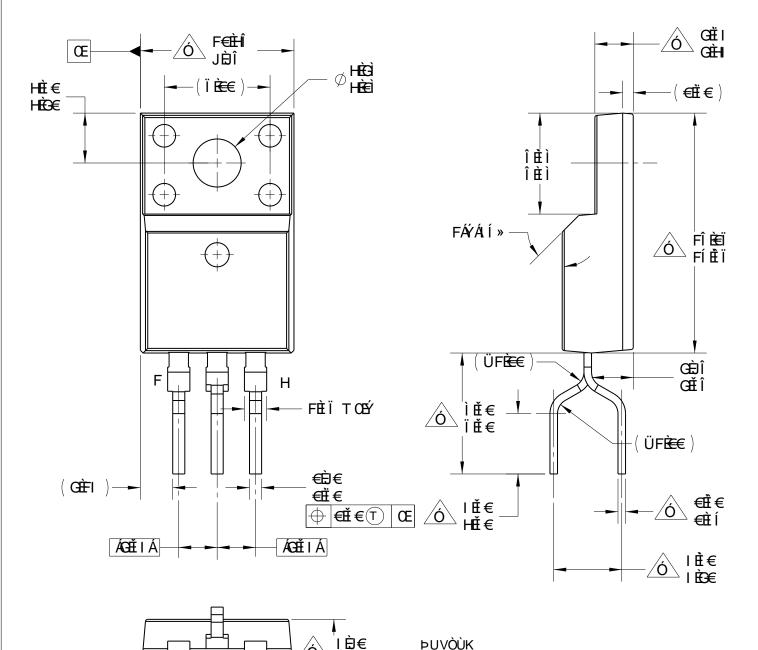


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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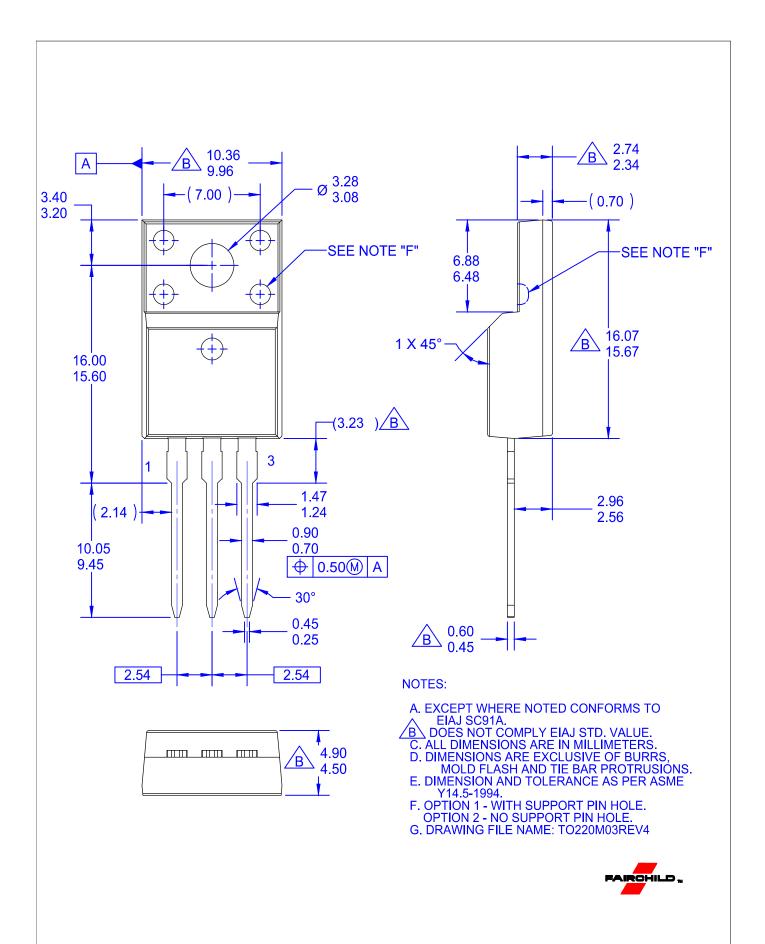
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